



SSO Noise And Conducted EMI: Modeling, Analysis, And Design Solutions

**Patrice Joubert Doriol¹, Aurora Sanna¹,
Akhilesh Chandra², Cristiano Forzan¹, and Davide Pandini¹**

¹STMicroelectronics, Central CAD and Solutions, Agrate Brianza, Italy

²STMicroelectronics, Central CAD and Solutions, Greater Noida, India

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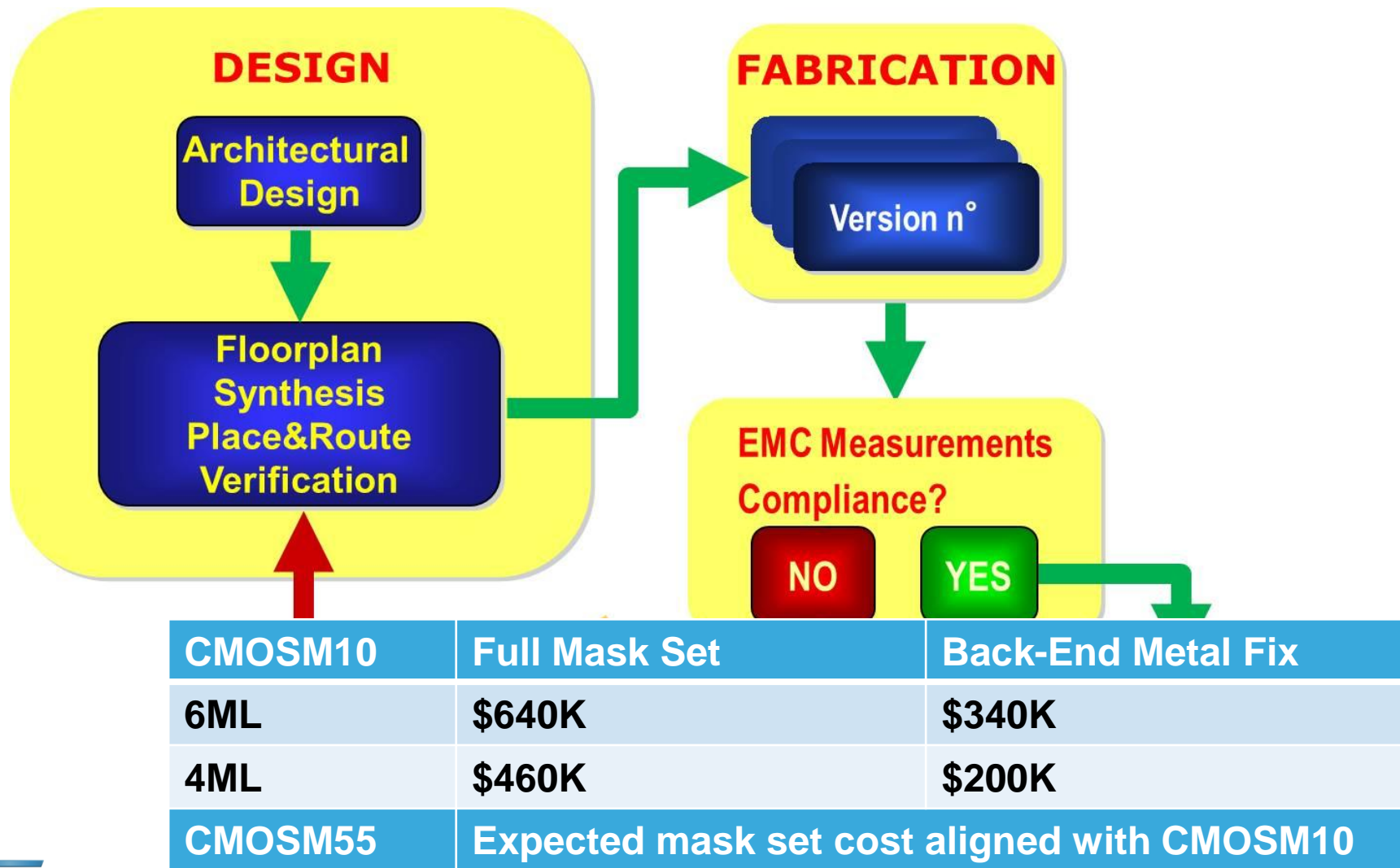
Today's I/Os Challenges

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- Higher I/O account
- Increasing operating frequencies
- Faster signal edge rates
- High I/O density makes it difficult to place PCB decaps close enough to the pads
- Automotive specific challenge: I/Os signal conducted EMI
- EMC and signal integrity are another mandatory objective for first silicon success

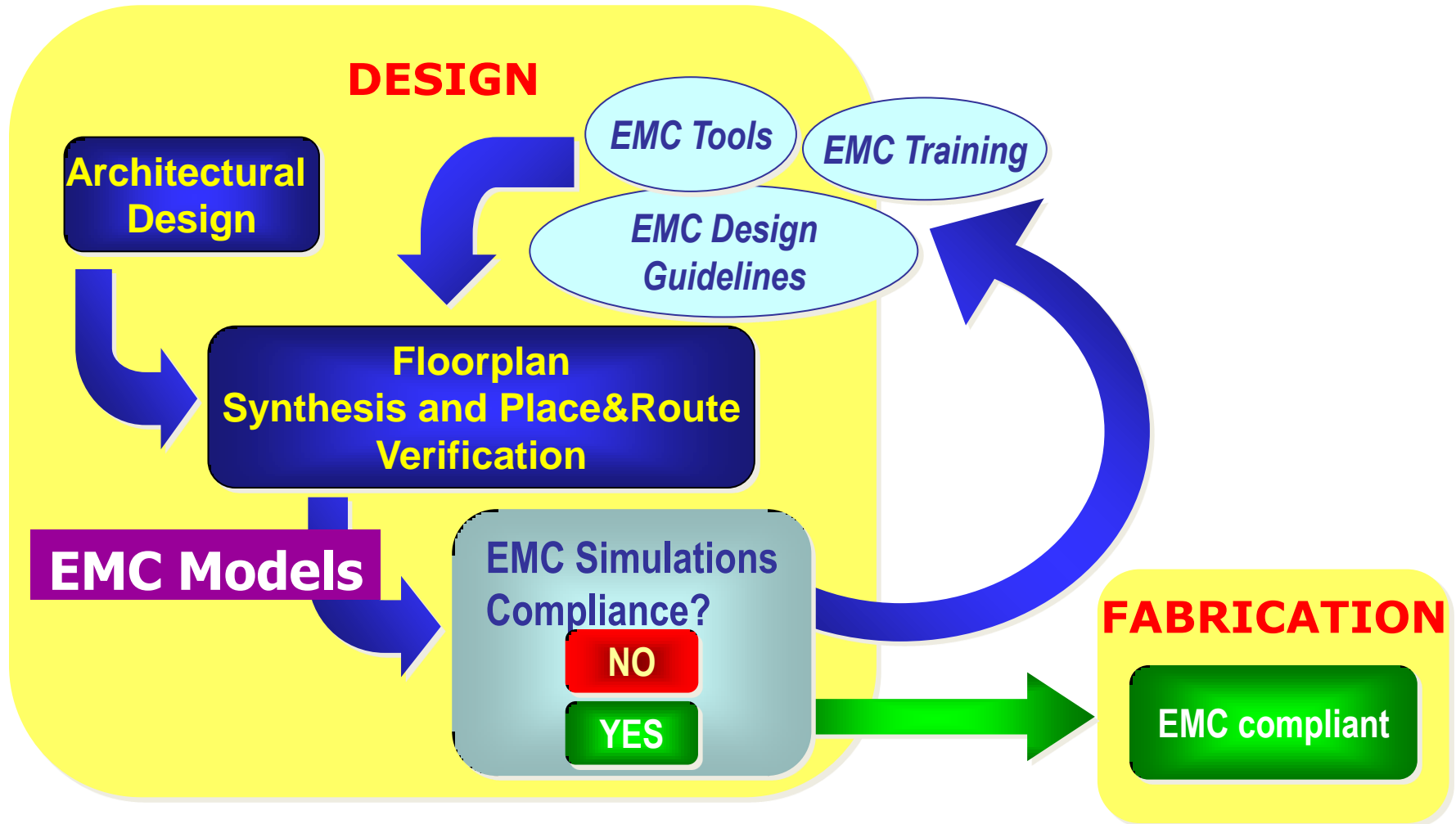
EMC At The End Of The Design Flow

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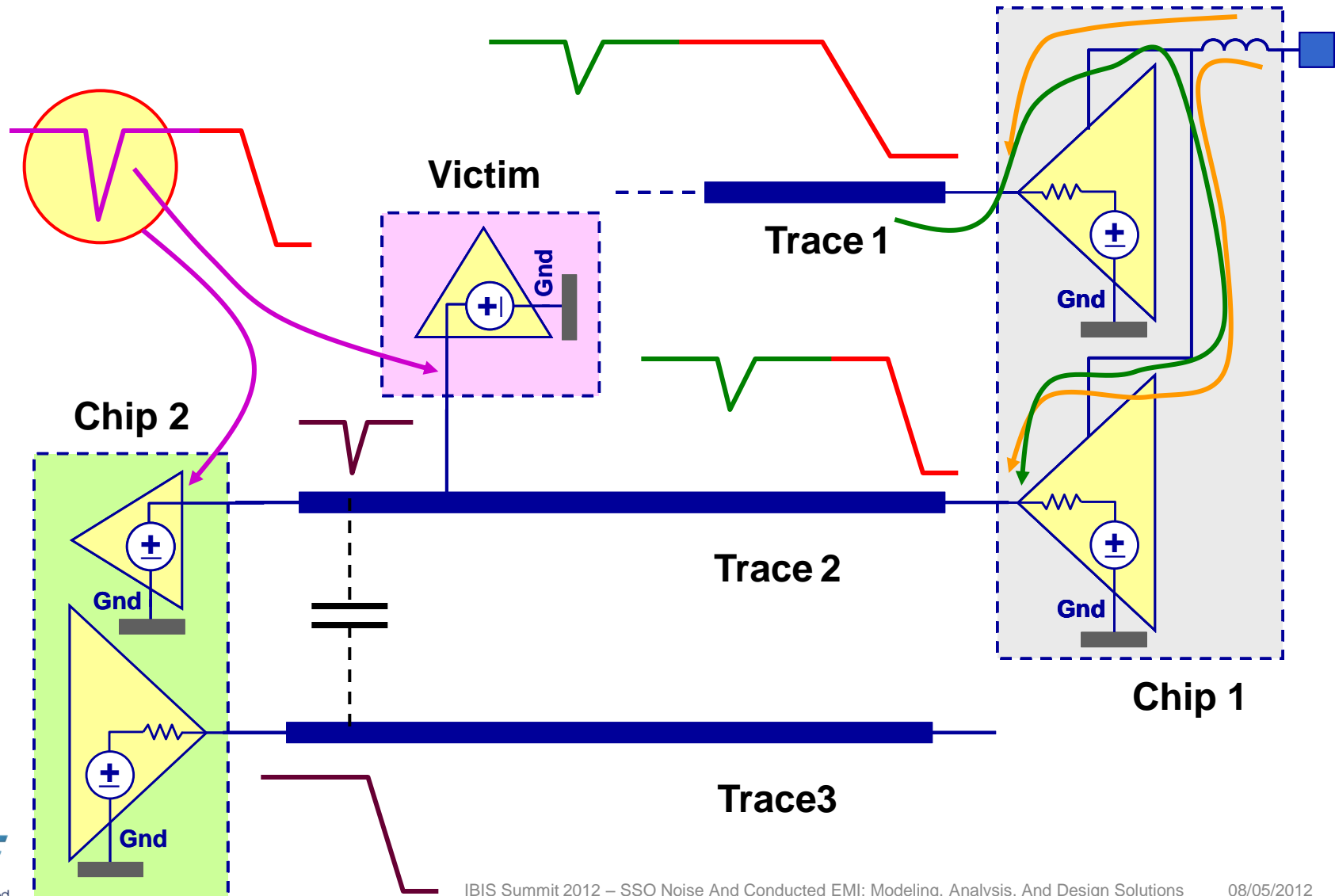
Our Vision: EMC-Aware Design

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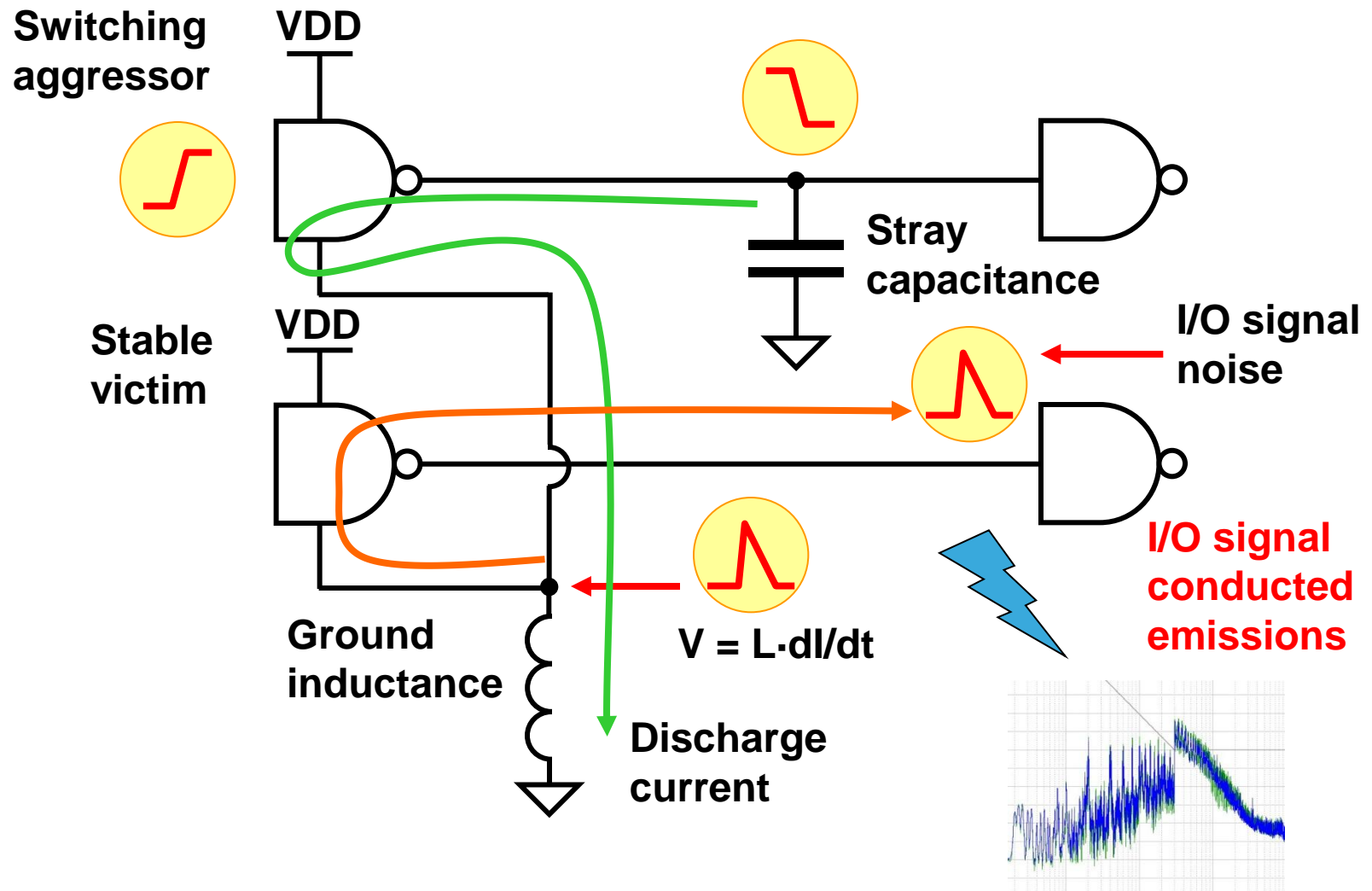
Reflection, Crosstalk, And SSO Noise

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SSO Noise And Conducted EMI

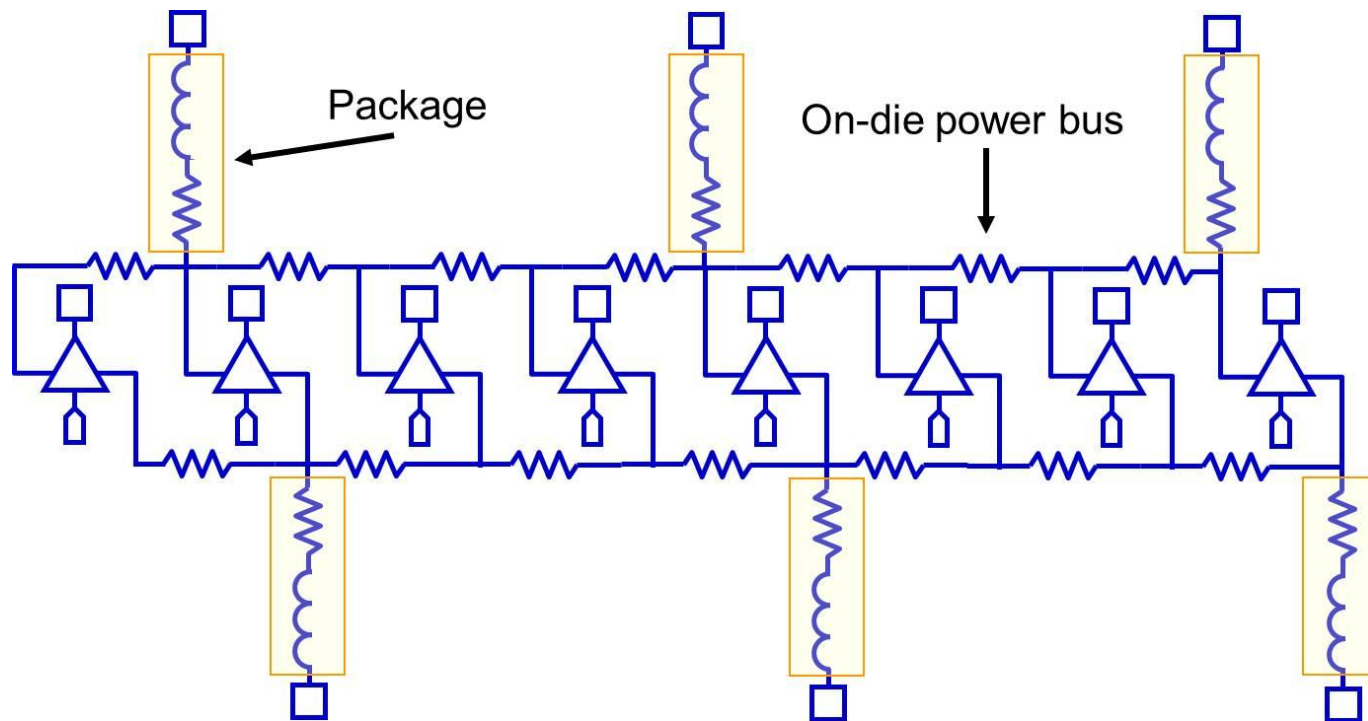
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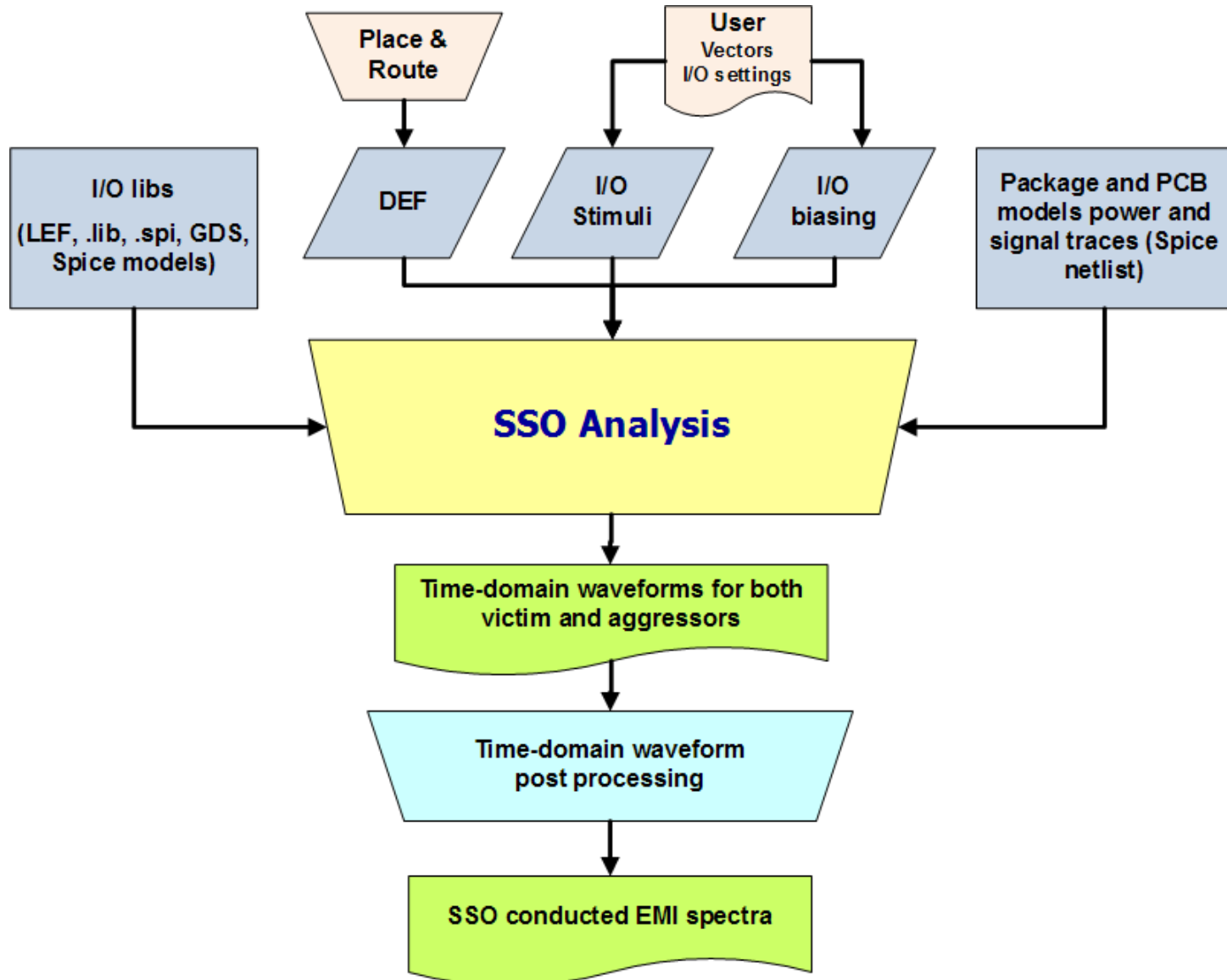


I/O Ring Circuit

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- Any realistic signal integrity and EMI simulation must include the complete system-level macromodel (die, package, board)
- A full transistor-level simulation of the I/O ring is impractical even for a limited number of adjacent toggling I/Os and a given victim

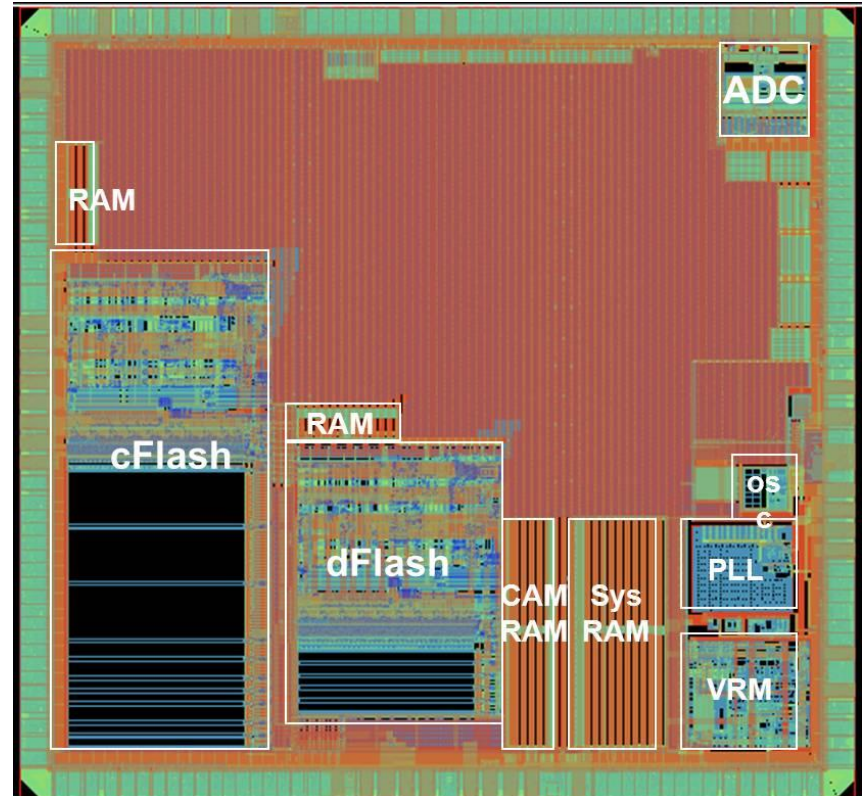




SSO Analysis For Automotive Applications

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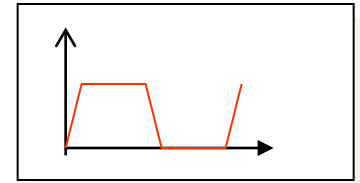
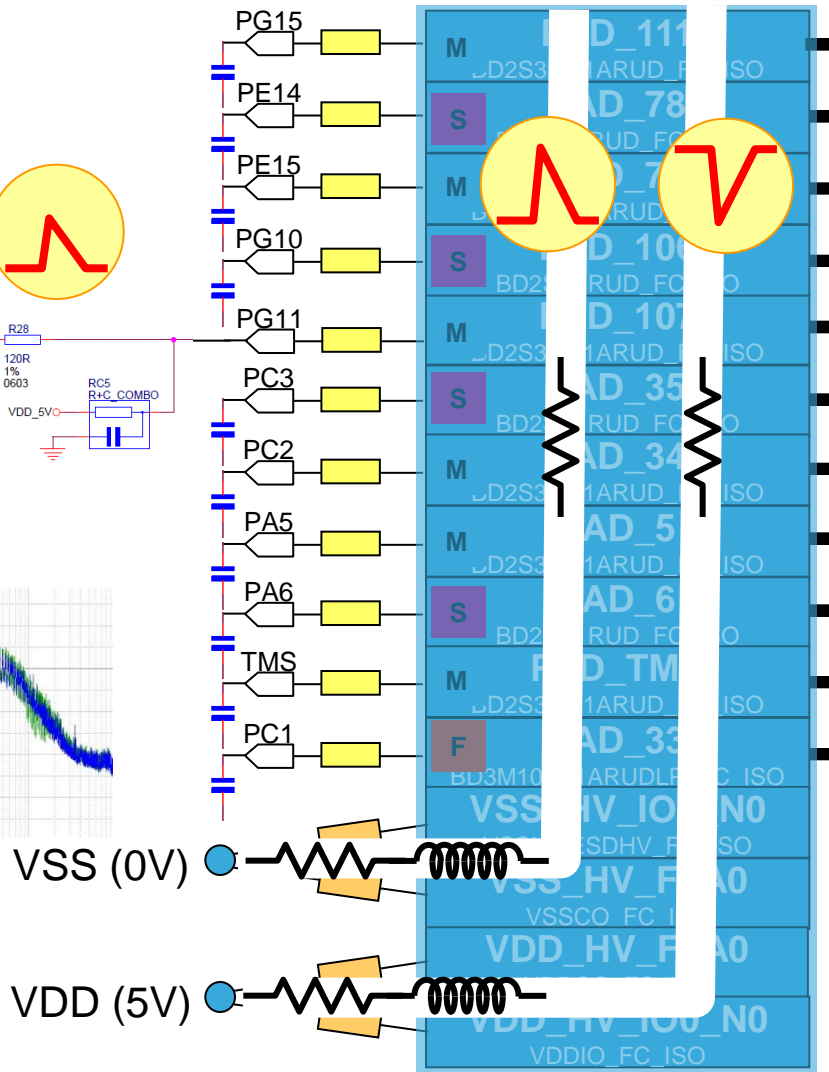
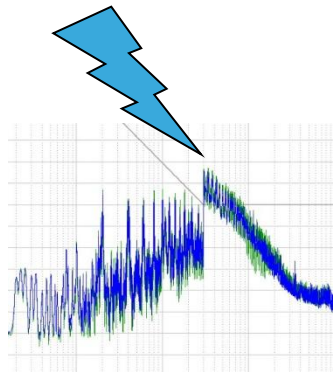
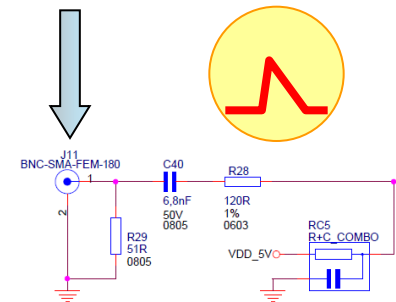
- **STYY**: Microcontroller in **CMOSM10-4ML**
- Size: $4.1 \times 4.1 = 16.81 \text{mm}^2$
- Instances: 365K
- Main Clock: 64MHz
- Package: LQFP144 (Wire bonding)



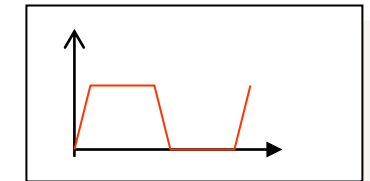
STYY I/O Bank For EMI Analysis

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Conducted
Emission
Test Pin



Stable Victim



Switching aggressors

Design Solutions For SSO Noise Reduction

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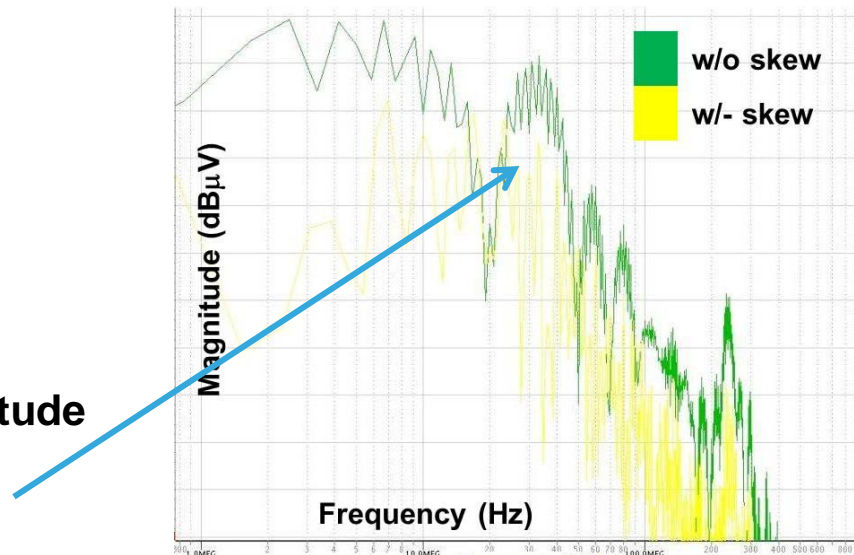
- I/Os' signal skewing
- I/O ring fillercap insertion
- I/O pads reduced driving strength
- I/O ring power/ground supply placement

I/O Skewing Impact on EMI

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- Typical I/Os' working frequency for automotive applications are in the range of a few KHz and do not need to toggle synchronously
 - A relative skew in the range of about 10ns is compatible with a correct functionality of the I/O ring
- Harmonic amplitude reduction of several dB μ Vs obtained in the frequency range of 1GHz

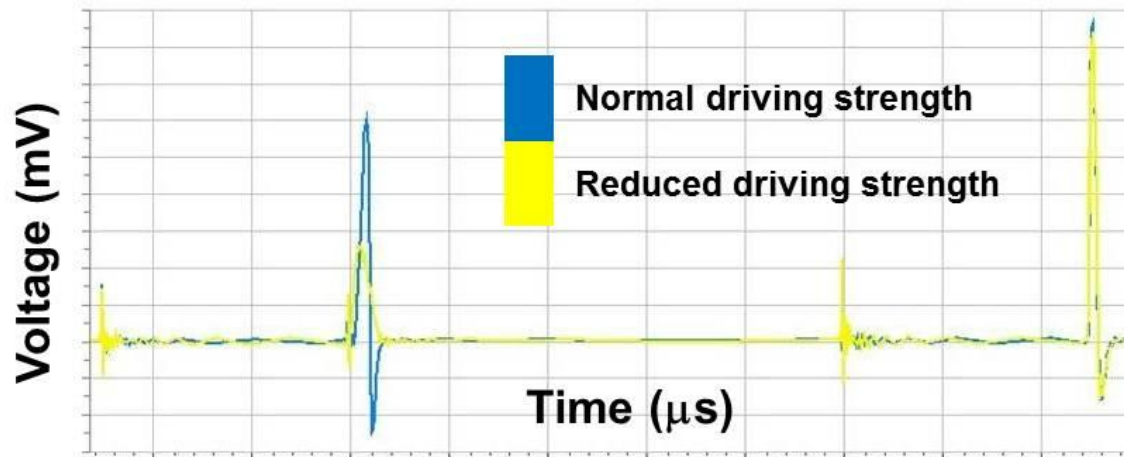
On some critical harmonics amplitude reduction of about 10dB μ V



I/O Filler caps Insertion And Driving Strength Reduction

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- I/O filler cap insertion did not prove to be an effective technique
 - Huge amount of decaps and related area to achieve only few dB μ V amplitude reduction
 - Difficult to exploit this technique on typical pad-limited I/O rings
- I/O driving strength reduction (when compliant with the timing constraints) from MEDIUM to SLOW strength version can further reduce the SSO noise



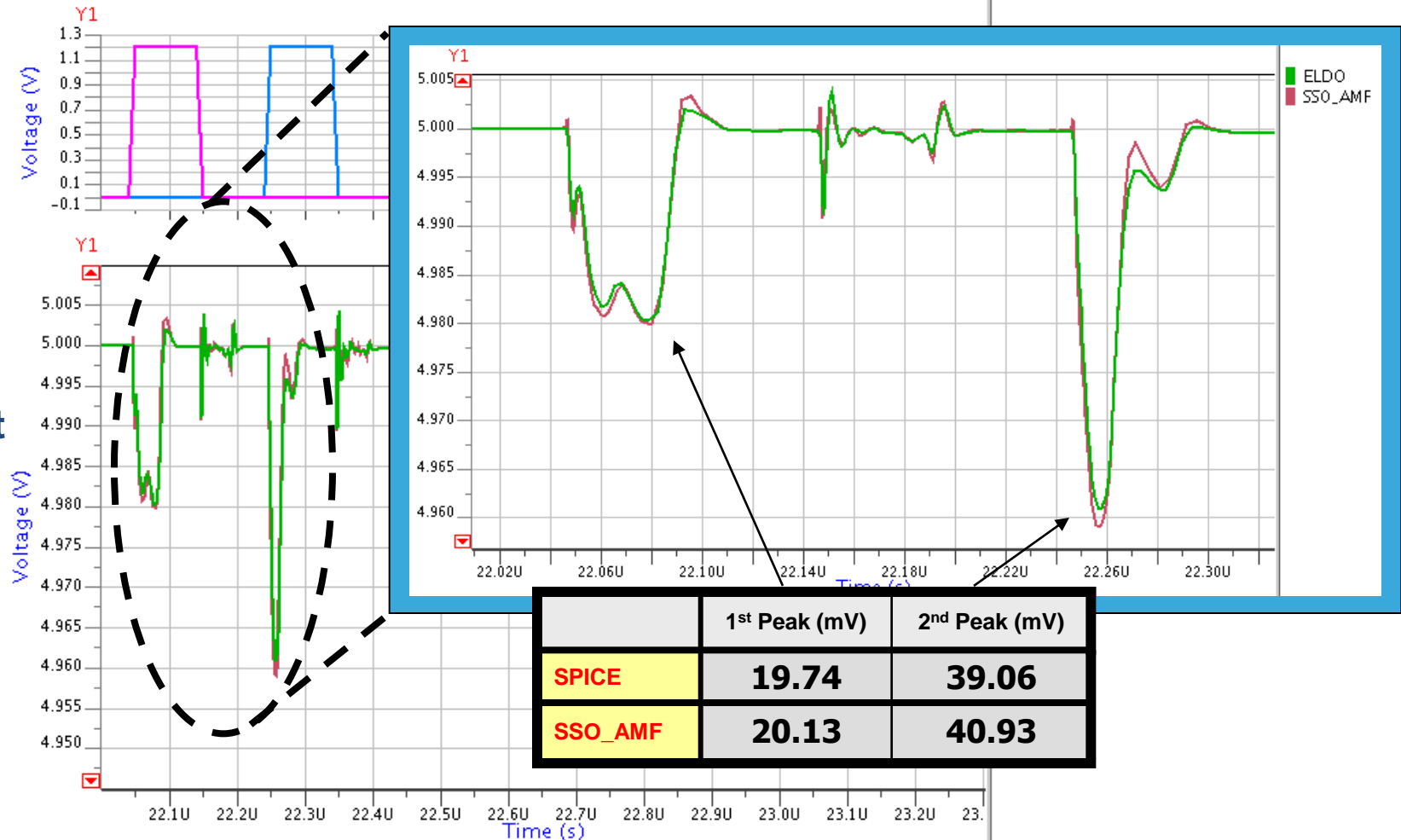
SSO Flow Validation

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- The gate-level SSO flow was validated vs. full Spice-level simulations

Aggr.
PADs
Input

Victim
PAD
Output



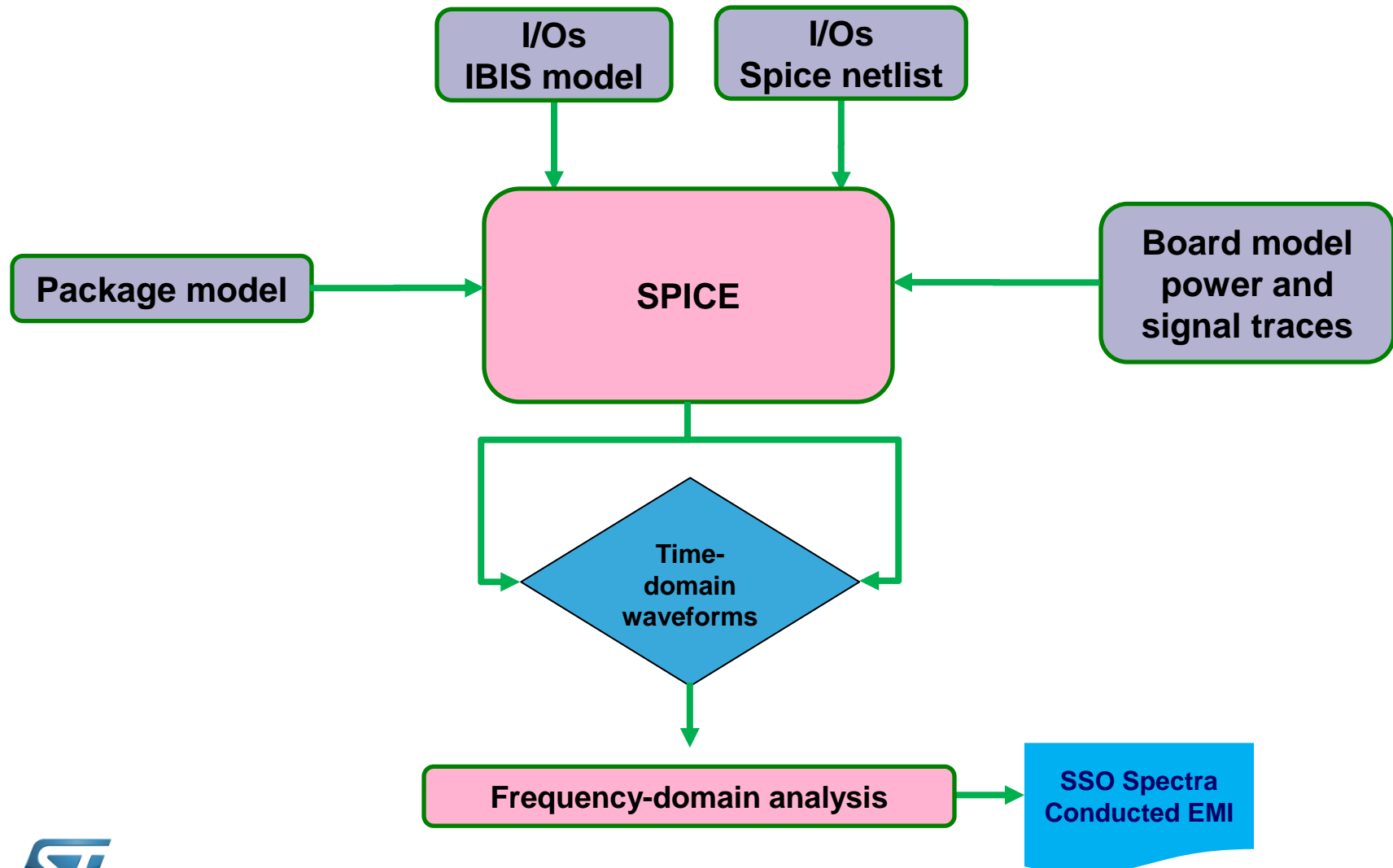
IBIS For SSO And EMI Analysis

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- Traditionally IBIS models have been used for signal integrity simulations on system PCBs
 - Behavioral modeling
 - IP protection
 - Fast simulation time
 - Reasonable accuracy
- However IBIS v4.0 cannot include predriver and crossbar currents and I/O ring power/ground supply bouncing which is the dominant source of SSO and conducted EMI
- To validate IBIS v5.0 for EMI analysis the same STYY I/O bank was used
- IBIS v5.0 was compared vs. full transistor-level simulations

IBIS Validation Flow

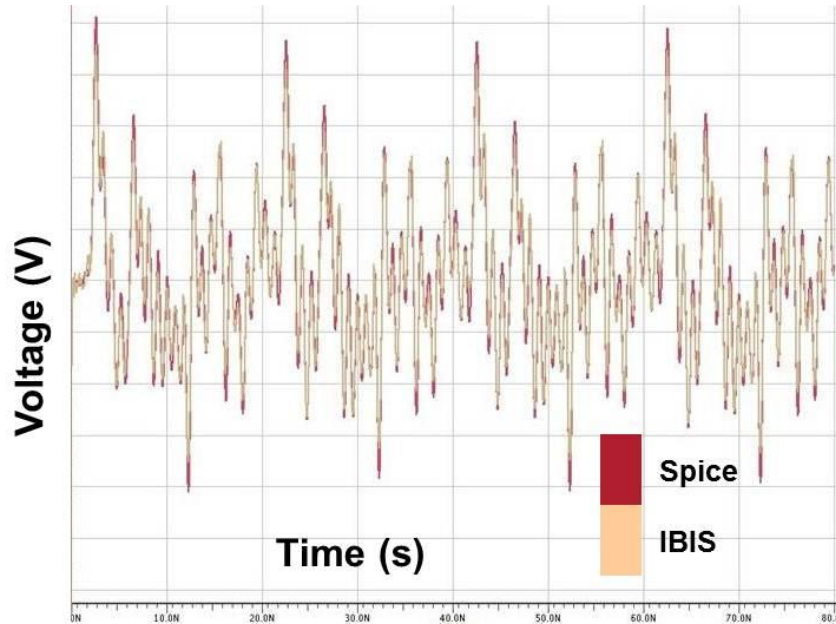
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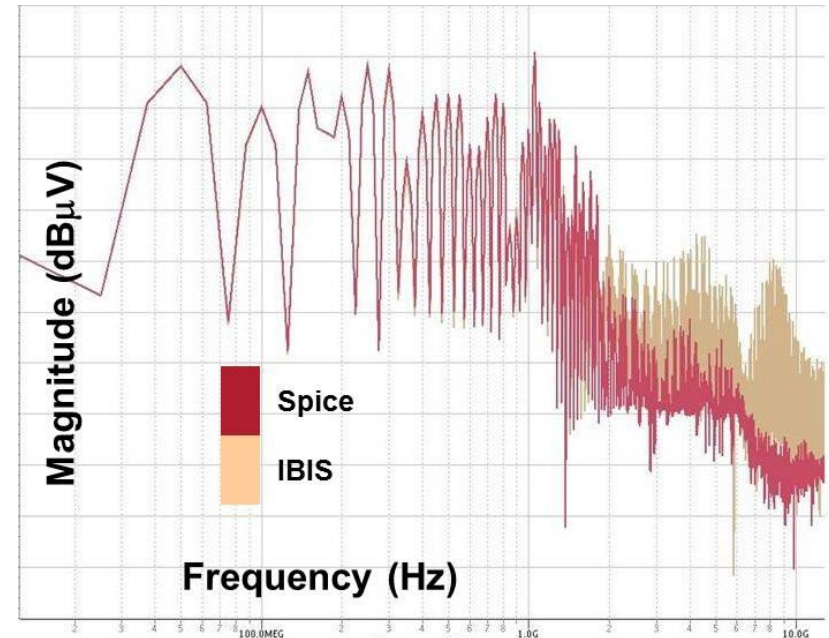
IBIS For SSO And EMI Analysis

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IBIS v5.0 vs. Spice



Time-domain analysis



Frequency-domain analysis

IBIS vs. Spice: good accuracy up to 2GHz

- CAD flow and design solutions for SSO and I/O conducted EMI analysis and optimization were presented
- Methodology exploited on an industrial automotive microcontroller in ST 90nm with eNVM technology
- IBIS v5.0 can be used for a reliable SSO and EMI analysis